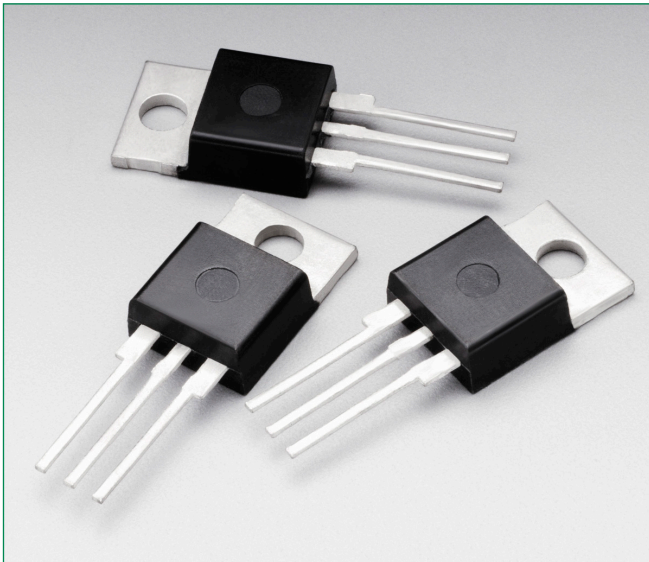


## BTB08-600CW3G, BTB08-800CW3G



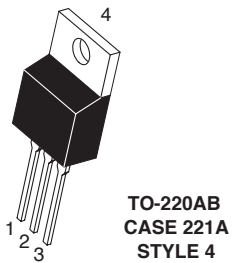
### Description

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

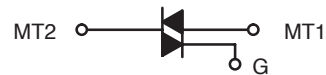
### Features

- Blocking Voltage to 800 V
- On-State Current Rating of 8 A RMS at 80°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt – 1500 V/s minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dI/dt – 3.0 A/ms minimum at 125°C
- These Devices are Pb-Free

### Pin Out



### Functional Diagram



### Additional Information



[Datasheet](#)



[Resources](#)



[Samples](#)

### Maximum Ratings † (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Part Number	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T <sub>J</sub> = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	BTB08-600CW3G	V <sub>DRM</sub>	600	V
	BTB08-800CW3G	V <sub>RRM</sub>	800	
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, TC = 80°C)		I <sub>T (RMS)</sub>	8.0	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = 25°C)		I <sub>TSM</sub>	90	A
Circuit Fusing Considerations (t = 10 ms)		I <sup>2</sup> t	36	A <sup>2</sup> sec
Non-Repetitive Surge Peak Off-State Voltage (T <sub>J</sub> = 25°C, t = 10ms)		V <sub>DSM</sub> , V <sub>RSM</sub>	V <sub>DRM</sub> √V <sub>RRM</sub> +100	V
Peak Gate Current (T <sub>J</sub> = 125°C, t = 20ms)		I <sub>GM</sub>	4.0	A
Peak Gate Power (Pulse Width ≤ 1.0 μs, TC = 80°C)		P <sub>GM</sub>	20	W
Average Gate Power (T <sub>J</sub> = 125°C)		P <sub>G(AV)</sub>	1.0	W
Operating Junction Temperature Range		T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C

† Indicates JEDEC Registered Data

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

### Maximum Ratings † (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC)	R <sub>θJC</sub>	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	60	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T <sub>L</sub>	260	°C

† Indicates JEDEC Registered Data

### Electrical Characteristics - OFF ( $T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Repetitive Blocking Current ( $V_D = V_{DRM} = V_{RRM}$ ; Gate Open)	$T_J = 25^\circ\text{C}$	$I_{DRM}^*$	-	-	0.005	mA
	$T_J = 125^\circ\text{C}$	$I_{RRM}$	-	-	1.0	

### Electrical Characteristics - ON

Characteristic		Symbol	Min	Typ	Max	Unit
Peak On-State Voltage (Note 2) ( $I_{TM} = \pm 11$ A Peak)		$V_{TM}$	-	-	1.55	V
Gate Trigger Current (Continuous dc) ( $V_D = 12$ V, $R_L = 30$ $\Omega$ )	MT2(+), G(+)	$I_{GT}$	2.5	-	35	mA
	MT2(+), G(-)		2.5	-	35	
	MT2(-), G(-)		2.5	-	35	
Holding Current ( $V_D = 12$ V, Gate Open, Initiating Current = $\pm 100$ mA)		$I_H$	-	-	45	mA
Latching Current ( $V_D = 24$ V, $I_G = 42$ mA)	MT2(+), G(+)	$I_L$	-	-	50	mA
	MT2(+), G(-)		-	-	80	
	MT2(-), G(-)		-	-	50	
Gate Trigger Voltage ( $V_D = 12$ V, $R_L = 30$ $\Omega$ )	MT2(+), G(+)	$V_{GT}$	0.5	-	1.7	V
	MT2(+), G(-)		0.5	-	1.1	
	MT2(-), G(-)		0.5	-	1.1	
Gate Non-Trigger Voltage ( $T_J = 125^\circ\text{C}$ )	MT2(+), G(+)	$V_{GD}$	0.2	-	-	V
	MT2(+), G(-)		0.2	-	-	
	MT2(-), G(-)		0.2	-	-	

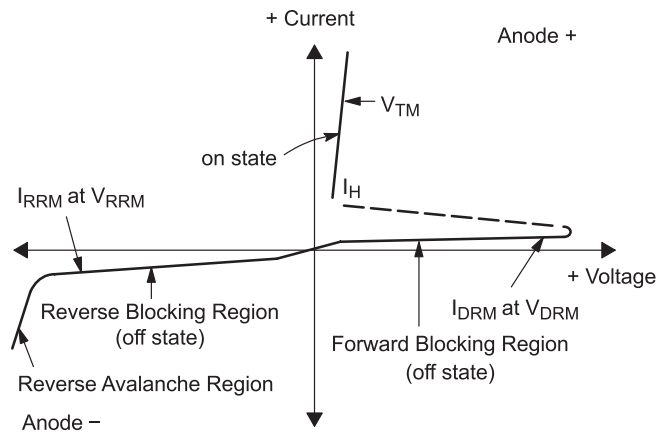
2. Indicates Pulse Test: Pulse Width  $\leq 2.0$  ms, Duty Cycle  $\leq 2\%$ .

### Dynamic Characteristics

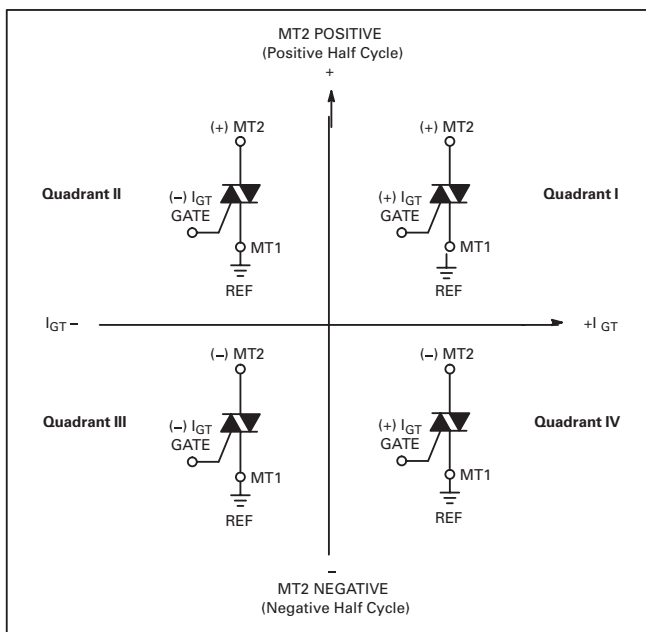
Characteristic	Symbol	Min	Typ	Max	Unit
Rate of Change of Commutating Current, See Figure 10. (Gate Open, T <sub>J</sub> = 125°C, No Snubber)	(di/dt) <sub>C</sub>	3.0	–	–	A/ms
Critical Rate of Rise of On-State Current (T <sub>J</sub> = 125°C, f = 120 Hz, I <sub>G</sub> = 2 x I <sub>GT</sub> , tr ≤ 100 ns)	di/dt	–	–	50	A/μs
Critical Rate-of-Rise of Off-State Voltage (V <sub>D</sub> = 0.66 x V <sub>DRM</sub> , Exponential Waveform, Gate Open, T <sub>J</sub> = 125°C)	dv/dt(c)	1500	–	–	V/μs

### Voltage Current Characteristic of SCR

Symbol	Parameter
V <sub>DRM</sub>	Peak Repetitive Forward Off State Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
V <sub>RRM</sub>	Peak Repetitive Reverse Off State Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
V <sub>TM</sub>	Maximum On State Voltage
I <sub>H</sub>	Holding Current

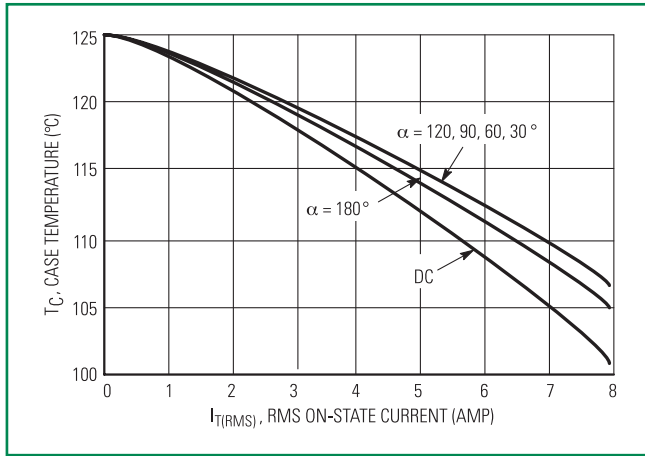


### Quadrant Definitions for a Triac

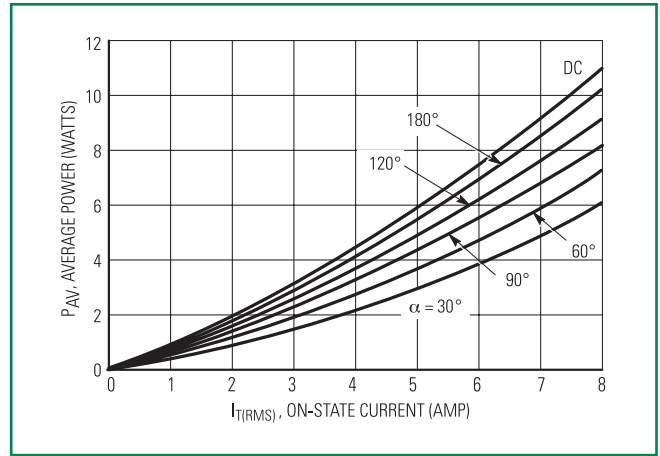


All polarities are referenced to MT1.  
With in-phase signals (using standard AC lines) quadrants I and III are used.

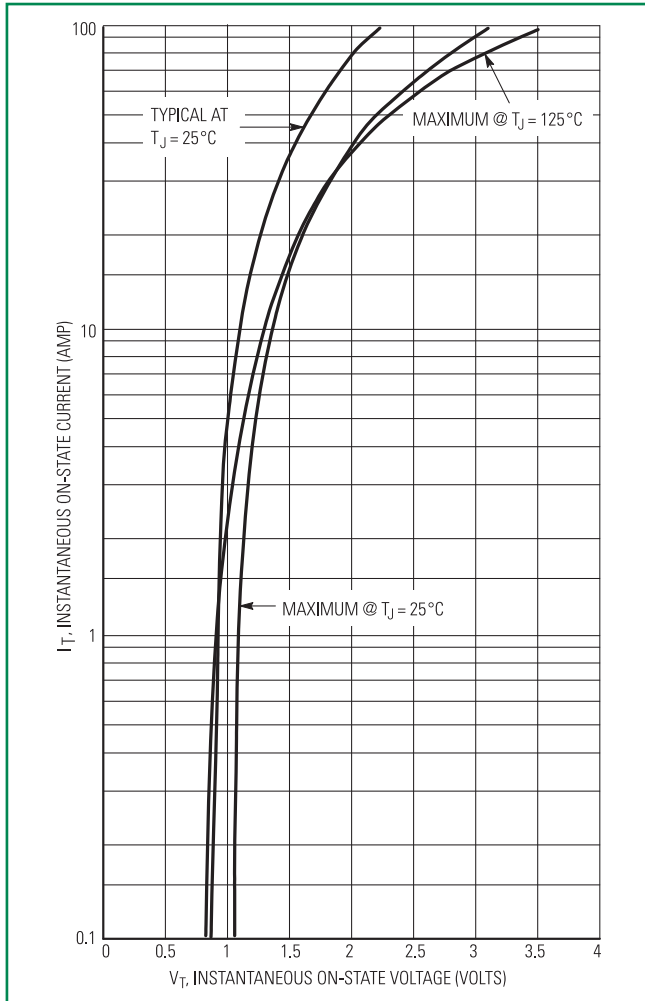
**Figure 1. RMS Current Derating**



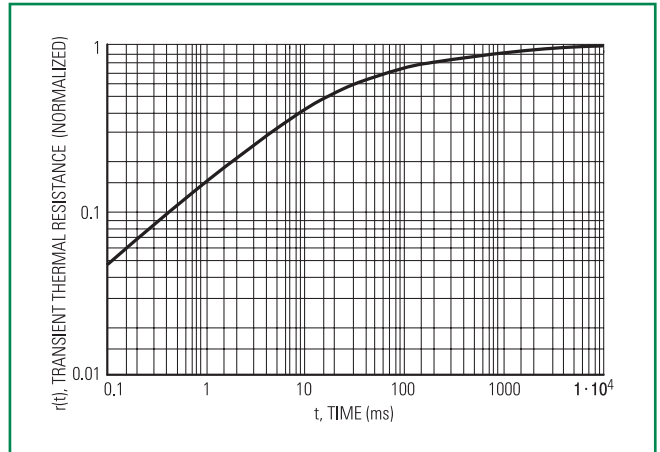
**Figure 2. On-State Power Dissipation**



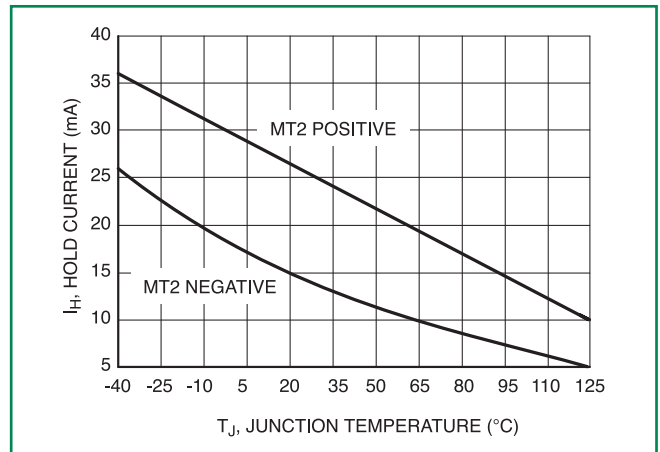
**Figure 3. On-State Characteristics**



**Figure 4. Thermal Response**

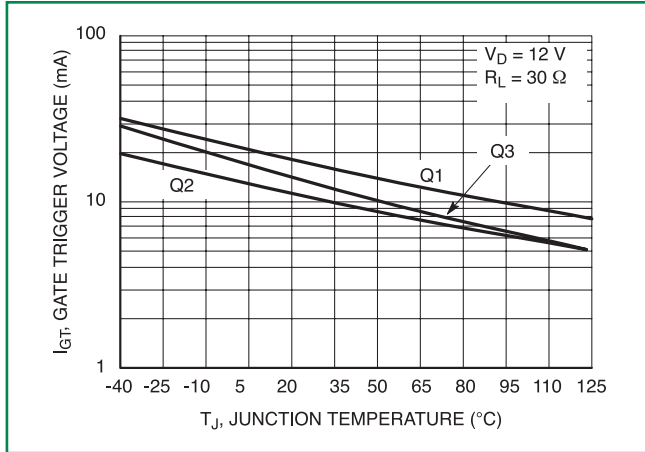


**Figure 5. Typical Hold Current Variation**

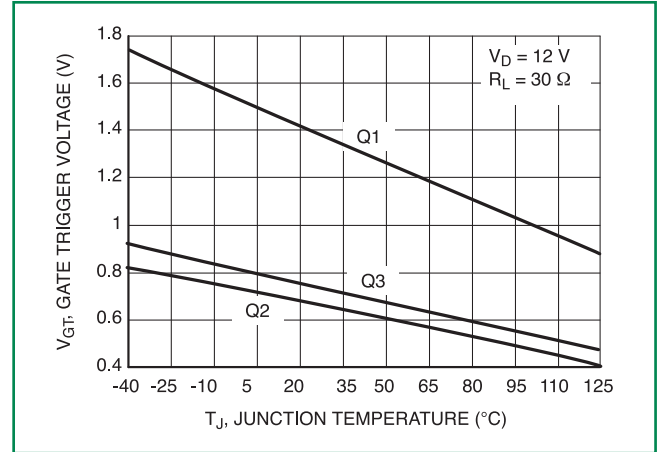


### Typical Characteristics

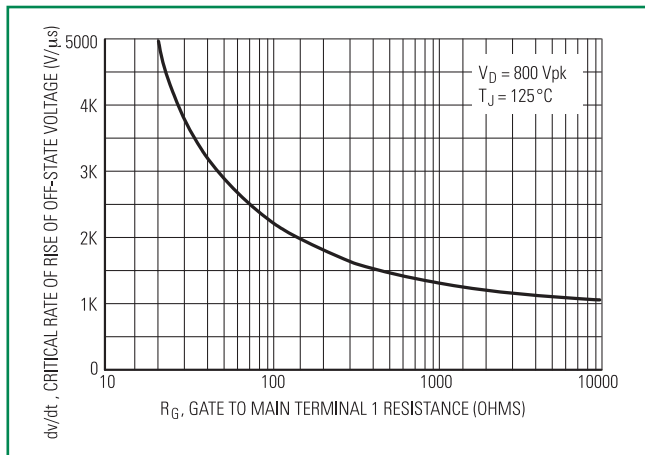
**Figure 6. Typical Gate Trigger Current Variation**



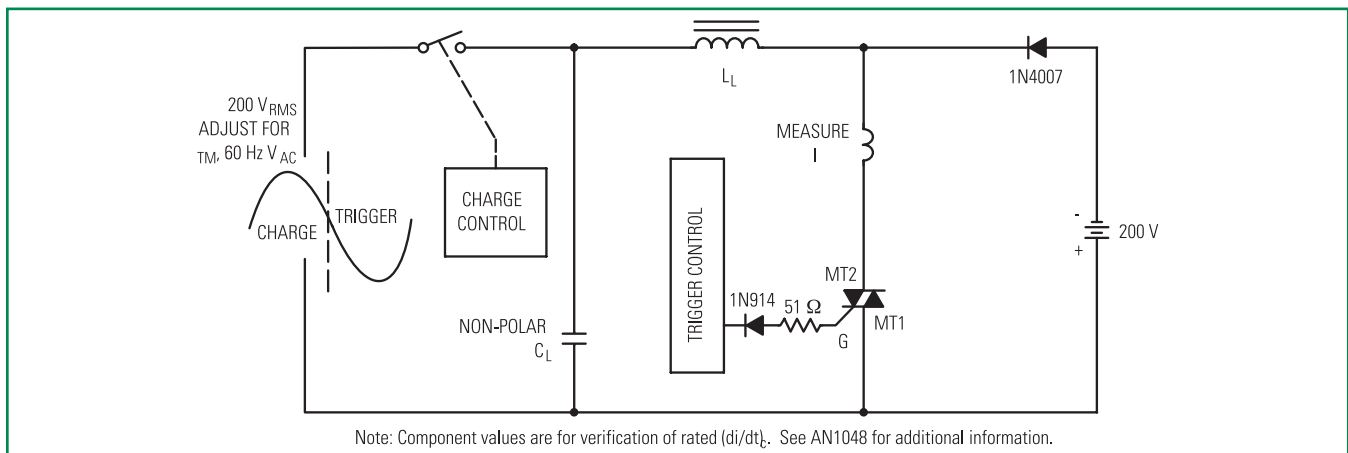
**Figure 7. Typical Gate Trigger Voltage Variation**



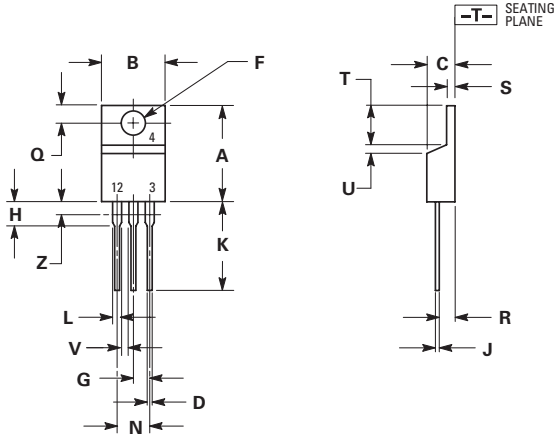
**Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)**



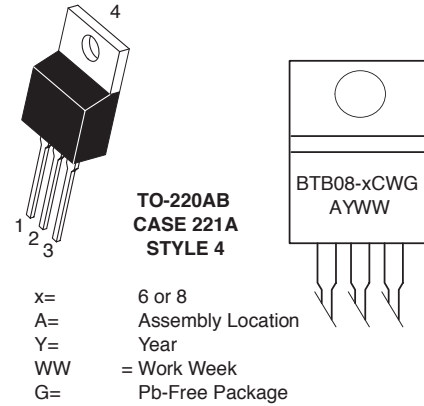
**Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current ( $di/dt$ )<sub>c</sub>**



### Dimensions



### Part Marking System



Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

### Pin Assignment

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

### Ordering Information

Device	Package	Shipping
BTB08-600CW3G	TO-220AB (Pb-Free)	50 Units / Retail
BTB08-800CW3G		

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